

MITSUBISHI IGBT MODULES  
**CM600DU-24NF**

HIGH POWER SWITCHING USE

**CM600DU-24NF**



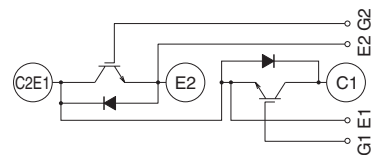
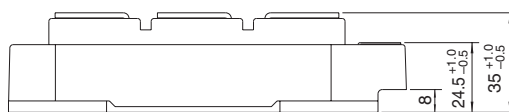
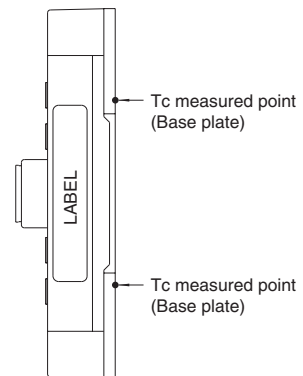
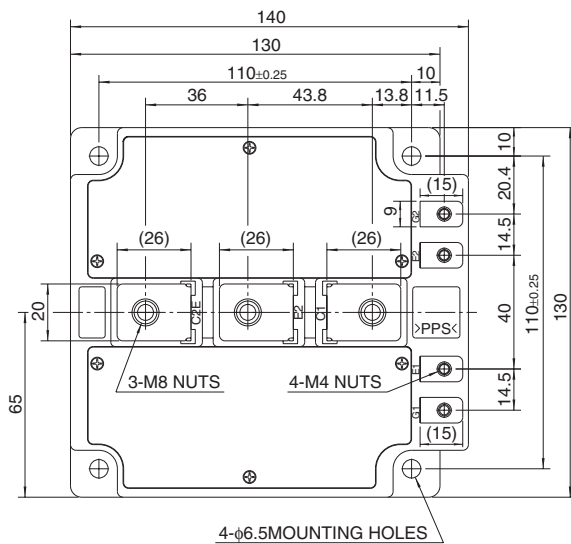
- IC ..... 600A
- VCES ..... 1200V
- Insulated Type
- 2-elements in a pack

**APPLICATION**

General purpose inverters & Servo controls, etc

**OUTLINE DRAWING & CIRCUIT DIAGRAM**

Dimensions in mm



CIRCUIT DIAGRAM

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**MAXIMUM RATINGS** (Tj = 25°C, unless otherwise specified)

Symbol	Parameter	Conditions	Rating	Unit
V <sub>CES</sub>	Collector-emitter voltage	G-E Short	1200	V
V <sub>GES</sub>	Gate-emitter voltage	C-E Short	±20	V
I <sub>C</sub>	Collector current	DC, T <sub>c</sub> ' = 109°C <sup>3</sup>	600	A
I <sub>CM</sub>		Pulse (Note 2)	1200	A
I <sub>E</sub> (Note 1)	Emitter current		600	A
I <sub>EM</sub> (Note 1)		Pulse (Note 2)	1200	A
P <sub>C</sub> (Note 3)	Total power dissipation	T <sub>c</sub> = 25°C	2080	W
T <sub>j</sub>	Junction temperature		-40 ~ +150	°C
T <sub>stg</sub>	Storage temperature		-40 ~ +125	°C
V <sub>isol</sub>	Isolation voltage	Terminals to base plate, f = 60Hz, AC 1 minute, RMS	2500	V
—	Mounting torque	Main terminals M8 screw	8.8 ~ 10.8	N • m
—		Mounting to heat sink M6 screw	3.5 ~ 4.5	N • m
—		G(E) Terminal M4 screw	1.3 ~ 1.7	N • m
	Weight	Typical value	1200	g

**ELECTRICAL CHARACTERISTICS** (Tj = 25°C, unless otherwise specified)

Symbol	Parameter	Conditions	Limits			Unit
			Min.	Typ.	Max.	
I <sub>CES</sub>	Collector-emitter cut-off current	V <sub>CE</sub> = V <sub>CES</sub> , G-E short	—	—	1	mA
V <sub>GE(th)</sub>	Gate-emitter threshold voltage	I <sub>C</sub> = 60mA, V <sub>CE</sub> = 10V	6	7	8	V
I <sub>GES</sub>	Gate-emitter leakage current	±V <sub>GE</sub> = V <sub>GES</sub> , C-E short	—	—	0.5	μA
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> = 600A, V <sub>GE</sub> = 15V				V
		T <sub>j</sub> = 25°C	—	1.95	2.65	
		T <sub>j</sub> = 125°C	—	2.15	—	
C <sub>ies</sub>	Input capacitance	V <sub>CE</sub> = 10V	—	—	140	nF
C <sub>oes</sub>	Output capacitance	G-E short	—	—	12	nF
C <sub>res</sub>	Reverse transfer capacitance		—	—	2.7	nF
Q <sub>G</sub>	Gate charge	V <sub>CC</sub> = 600V, I <sub>C</sub> = 600A, V <sub>GE</sub> = 15V	—	4000	—	nC
t <sub>d(on)</sub>	Turn-on delay time		—	—	800	ns
t <sub>r</sub>	Rise time	V <sub>CC</sub> = 600V, I <sub>C</sub> = 600A	—	—	180	ns
t <sub>d(off)</sub>	Turn-off delay time	V <sub>GE</sub> = ±15V	—	—	900	ns
t <sub>f</sub>	Fall time	R <sub>G</sub> = 1.0Ω, Inductive load	—	—	350	ns
t <sub>rr</sub> (Note 1)	Reverse recovery time	I <sub>E</sub> = 600A	—	—	300	ns
Q <sub>rr</sub> (Note 1)	Reverse recovery charge		—	28	—	μC
V <sub>EC</sub> (Note 1)	Emitter-collector voltage	I <sub>E</sub> = 600A, G-E short	—	—	3.35	V
R <sub>th(j-c)Q</sub>	Thermal resistance*1	IGBT part (1/2 module)	—	—	0.06	K/W
R <sub>th(j-c)R</sub>		FWDi part (1/2 module)	—	—	0.11	K/W
R <sub>th(c-f)</sub>	Contact thermal resistance	Case to heat sink, Thermal compound Applied*2 (1/2 module)	—	0.019	—	K/W
R <sub>th(j-c)Q</sub>	Thermal resistance	Case temperature measured point is just under the chips	—	—	0.023*3	K/W
R <sub>G</sub>	External gate resistance		1.0	—	10	Ω

\*1 : Case temperature (T<sub>c</sub>) measured point is shown in page OUTLINE DRAWING.

\*2 : Typical value is measured by using thermally conductive grease of λ = 0.9[W/(m • K)].

\*3 : Case temperature (T<sub>c</sub>) measured point is just under the chips.

If you use this value, R<sub>th(f-a)</sub> should be measured just under the chips.

Note 1. I<sub>E</sub>, V<sub>EC</sub>, t<sub>rr</sub> & Q<sub>rr</sub> represent characteristics of the anti-parallel, emitter-collector free-wheel diode (FWDi).

2. Pulse width and repetition rate should be such that the device junction temperature (T<sub>j</sub>) does not exceed T<sub>jmax</sub> rating.

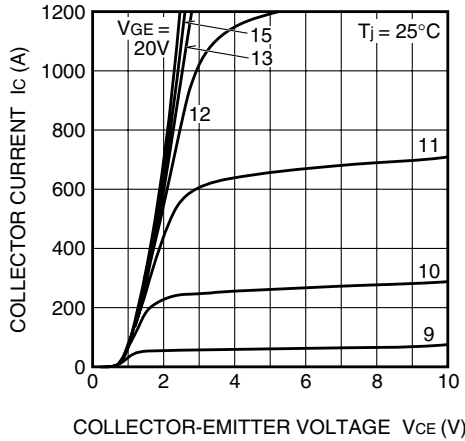
3. Junction temperature (T<sub>j</sub>) should not increase beyond 150°C.

CM600DU-24NF

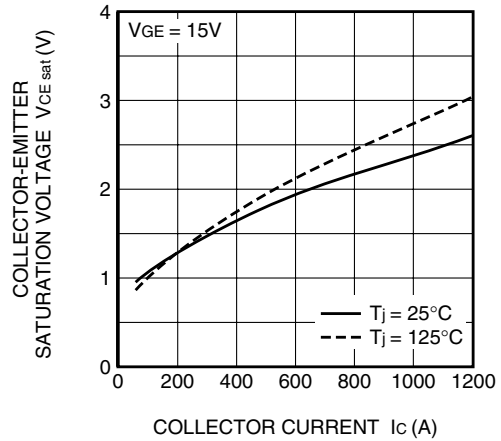
HIGH POWER SWITCHING USE

PERFORMANCE CURVES

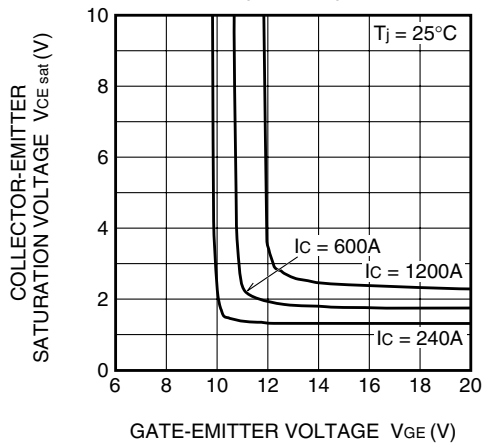
OUTPUT CHARACTERISTICS (TYPICAL)



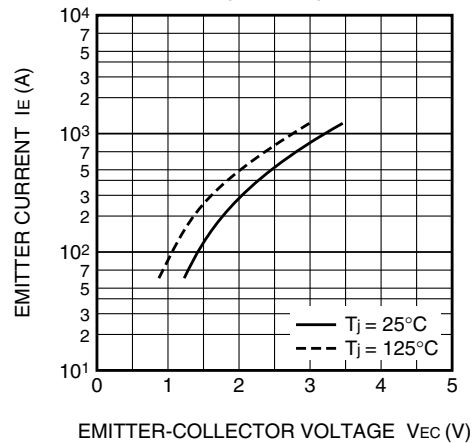
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



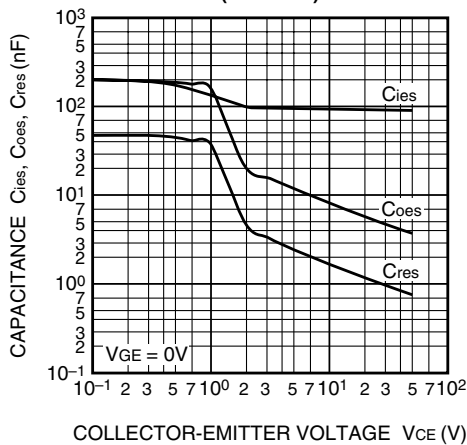
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



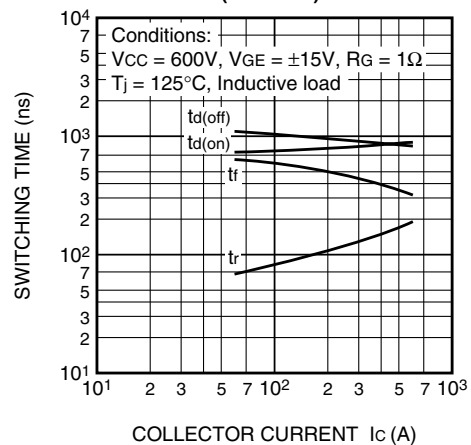
FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)



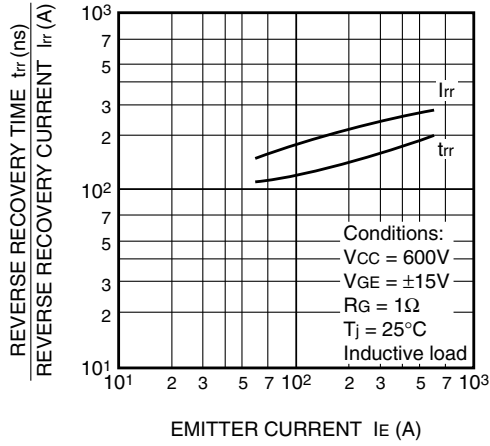
CAPACITANCE-VCE CHARACTERISTICS (TYPICAL)



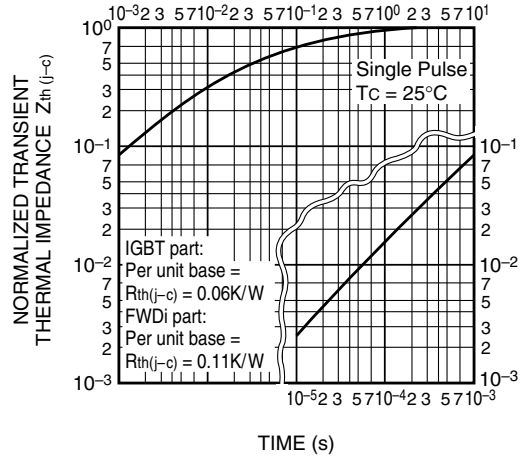
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)



REVERSE RECOVERY CHARACTERISTICS OF FREE-WHEEL DIODE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (IGBT part & FWDi part)



GATE CHARGE CHARACTERISTICS (TYPICAL)

